

**1A 30V(1.00mm)**

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**Chip Information**

Chip Size	1.00 x 1.00mm
Pad Size	0.89 x 0.89mm
Chip Quantity	10928 pcs/wafer
Scribe Line Width	50um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM	30	V	
Maximum DC Blocking Voltage	VR	30	V	
Average Forward Rectified Current	IF(AV)	1000	mA	
Peak Forward Surge Current	IFSM	10	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.450	0.440	0.405	V	IF=700mA Ta=25degC
	VF2	0.350	0.340	0.320	V	IF=100mA Ta=25degC
	VF3	0.430	0.425	0.380	V	IF=500mA Ta=25degC
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	10	8	1.5	uA	VR=5V Ta=25degC
	IR2	60	40	20	uA	VR=30V Ta=25degC
	IR3	20	15	3	uA	VR=15V Ta=25degC
	IR4				uA	
Reverse Breakdown Voltage	BV	30	34	45	V	IR=500uA
Junction Capacitance	Cj			67	pF	VR=10V,f=1MHz
Reverse Recovery Time	trr				nS	

**Ordering Information**

Chip Type	Chip Thickness	Back Metal
XFH715	180 +/- 20um	Au(For Eutectic)
XFH717	150 +/- 20um	Au(For Eutectic)
XFH716	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:  
Designed For FS1J3